

**Type 2N3866A**  
**Geometry 1007**  
**Polarity NPN**  
**Qual Level: JAN - JANS**

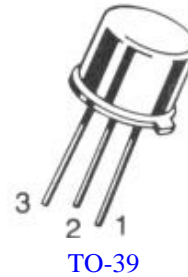
**Generic Part Number:**  
**2N3866A**

**REF: MIL-PRF-19500/398**

**Features:**

[Request Quotation](#)

- General-purpose silicon transistor for switching and amplifier applications.
- Housed in [TO-39](#) case.
- Also available in chip form using the [1007](#) chip geometry.
- The Min and Max limits shown are per [MIL-PRF-19500/398](#) which Semicoa meets in all cases.



**Maximum Ratings**

$T_C = 25^{\circ}\text{C}$  unless otherwise specified

Rating	Symbol	Rating	Unit
Collector-Emitter Voltage	$V_{CEO}$	30	V
Collector-Base Voltage	$V_{CBO}$	60	V
Emitter-Base Voltage	$V_{EBO}$	3.5	V
Collector Current, Continuous	$I_C$	0.4	A
Operating Junction Temperature	$T_J$	-55 to +175	$^{\circ}\text{C}$
Storage Temperature	$T_{STG}$	-55 to +175	$^{\circ}\text{C}$

### Electrical Characteristics

$T_C = 25^\circ\text{C}$  unless otherwise specified

OFF Characteristics	Symbol	Min	Max	Unit
Collector-Base Breakdown Voltage $I_C = 100 \mu\text{A}$ , pulsed	$V_{(BR)CBO}$	60	---	V
Collector-Emitter Breakdown Voltage $I_C = 5 \text{ mA}$ , pulsed	$V_{(BR)CEO}$	30	---	V
Collector-Emitter Breakdown Voltage $I_C = 40 \text{ mA}$ , $V_{BE} = -5\text{V}$ , clamped	$V_{(BR)CEC}$	55	---	---
Emitter-Base Breakdown Voltage $I_E = 100 \mu\text{A}$ , pulsed	$V_{(BR)EBO}$	3.5	---	V
Collector-Emitter Cutoff Current $V_{CE} = 55 \text{ V}$	$I_{CES}$	---	100	$\mu\text{A}$
Collector-Emitter Cutoff Current $V_{CE} = 55 \text{ V}$ , $T_A = +150^\circ\text{C}$	$I_{CES2}$	---	2.0	mA
Collector-Emitter Cutoff Current $V_{CE} = 28 \text{ V}$	$I_{CEO}$	---	20	$\mu\text{A}$

ON Characteristics	Symbol	Min	Max	Unit
<b>Forward Current Transfer Ratio</b> $I_C = 50 \text{ mA}$ , $V_{CE} = 5.0 \text{ V}$ (pulsed)	$h_{FE1}$	25	200	---
$I_C = 360 \text{ mA}$ , $V_{CE} = 5.0 \text{ V}$ (pulsed)	$h_{FE2}$	8.0	---	---
$I_C = 50 \text{ mA}$ , $V_{CE} = 5.0 \text{ V}$ (pulsed), $T_A = -55^\circ\text{C}$	$h_{FE3}$	12	---	---
<b>Collector-Emitter Saturation Voltage</b> $I_C = 100 \text{ mA}$ , $I_B = 10 \text{ mA}$ (pulsed)	$V_{CE(sat)}$	---	1.0	V dc
<b>Power Output</b> $V_{CC} = 28 \text{ V}$ , $P_{IN} = 0.15 \text{ W}$ , $f = 400 \text{ MHz}$	$P_{1out}$	1.0	2.0	W
<b>Power Output</b> $V_{CC} = 28 \text{ V}$ , $P_{IN} = 0.075 \text{ W}$ , $f = 400 \text{ MHz}$	$P_{2out}$	0.5	---	W
<b>Collector Efficiency</b> $V_{CC} = 28 \text{ V}$ , $P_{IN} = 0.15 \text{ W}$ , $f = 400 \text{ MHz}$	$\eta_1$	45	---	%
<b>Collector Efficiency</b> $V_{CC} = 28 \text{ V}$ , $P_{IN} = 0.075 \text{ W}$ , $f = 400 \text{ MHz}$	$\eta_2$	40	---	%

Small Signal Characteristics	Symbol	Min	Max	Unit
<i>Magnitude of Common Emitter, Small Signal, Short Circuit</i> Current Transfer Ratio $I_C = 50 \text{ mA}$ , $V_{CE} = 15 \text{ V}$ , $f = 200$	$ h_{FE} $	4.0	7.5	---
<i>Open Circuit Output Capacitance</i> $V_{CB} = 28 \text{ V}$ , $I_E = 0$	$C_{OBO}$	---	3.5	pF

This datasheet has been downloaded from:

[www.DatasheetCatalog.com](http://www.DatasheetCatalog.com)

Datasheets for electronic components.



LittleDiode supplies new, hard to find or obsolete electronic components and semiconductors all over the world.

With over two million different components listed you are sure to find the part you need.

Feel free to visit us today at our online store:

[LittleDiode.com](http://LittleDiode.com)

Looking forward to providing you with the best possible service.